

SBD Type : FSQ10A06B

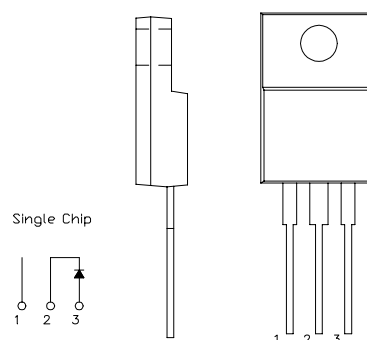
構造 : ショトキバリアダイオード (S B D)

Construction: Schottky Barrier Diode

用途 : 高周波整流用

Application : High Frequency Rectification

■ OUTLINE DRAWING



■ 最大定格 / Maximum Ratings

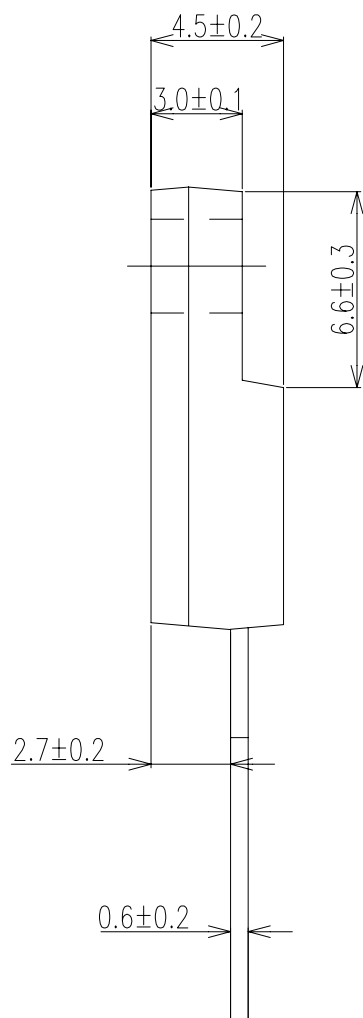
Approx Net Weight:1.75g

Rating	Symbol	FSQ10A06B			Unit
くり返しピーク逆電圧 Repetitive Peak Reverse Voltage	V_{RRM}	60			V
非くり返しピーク逆電圧 Non-repetitive Peak Reverse Voltage	V_{RSM}	65			V
平均整流電流 Average Rectified Output Current	I_O	10	Tc=111	50 Hz、正弦半波通電抵抗負荷 Half Sine Wave, Resistive Load	A
実効順電流 RMS Forward Current	$I_{F(RMS)}$	15.7			A
サージ順電流 Surge Forward Current	I_{FSM}	150	50 Hz 正弦半波, 1サイクル, 非くり返し Half Sine Wave, 1cycle, Non-repetitive		A
動作接合温度範囲 Operating Junction Temperature Range	T_{jw}	- 40 ~ + 150			
保存温度範囲 Storage Temperature Range	T_{stg}	- 40 ~ + 150			
締付けトルク Mounting torque	F_{tor}	(推奨値 recommended torque=0.5)			N・m

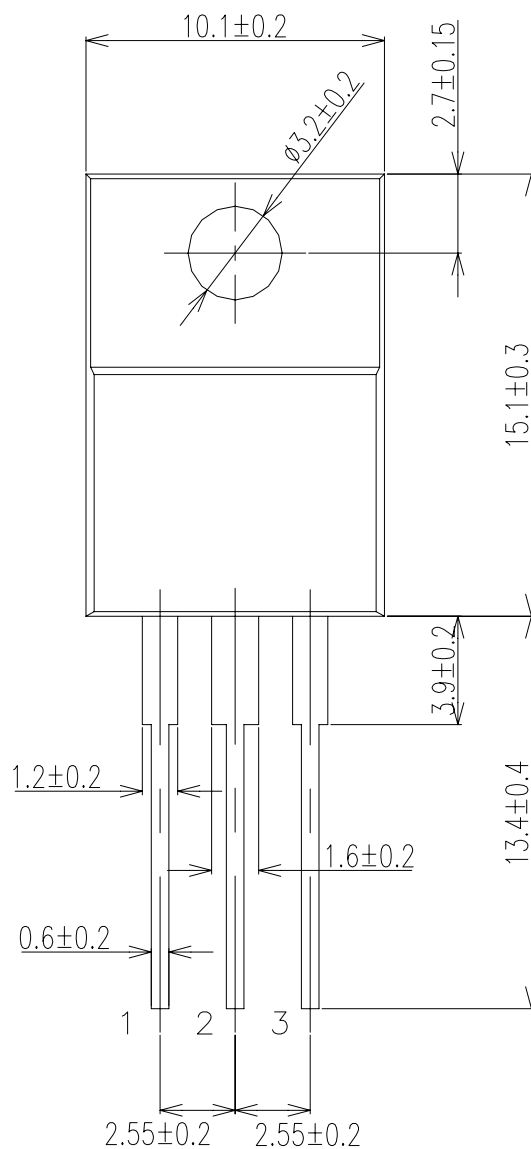
■ 電氣的・熱的特性 / Electrical・Thermal Characteristics

Characteristics	Symbol	Conditions	Min.	Typ.	Max.	Unit
ピーク逆電流 Peak Reverse Current	I_{RM}	$T_j = 25$, $V_{RM} = V_{RRM}$	-	-	10	mA
ピーク順電圧 Peak Forward Voltage	V_{FM}	$T_j = 25$, $I_{FM} = 10$ A	-	-	0.67	V
熱抵抗 Thermal Resistance	接合部・ケース間 Junction to Case	$R_{th(j-c)}$ Junction to Case	-	-	3	/W
	ケース・フィン間 Case to Fin	$R_{th(c-f)}$ Case to Fin	-	-	1.5	/W

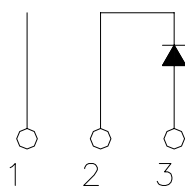
F S Q_A_B外形図 (mm)



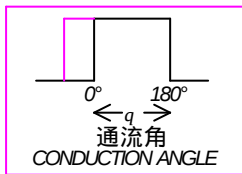
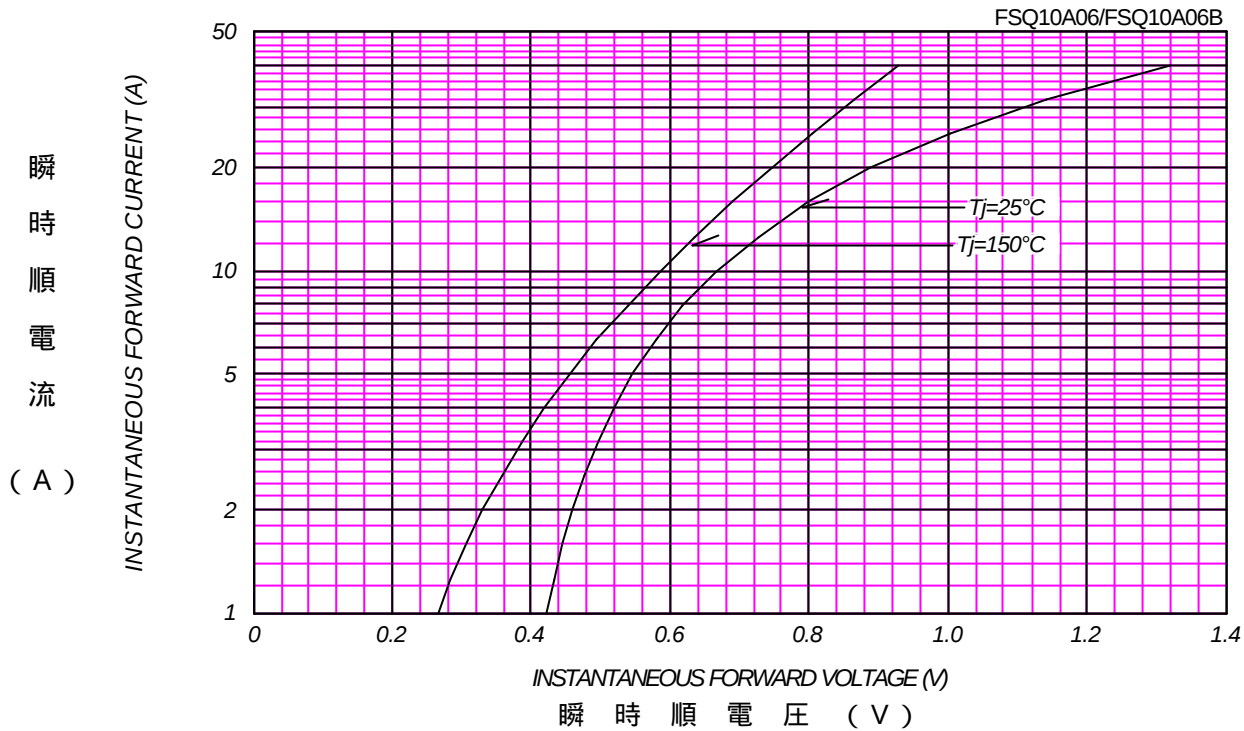
www.DataSheet4U.com



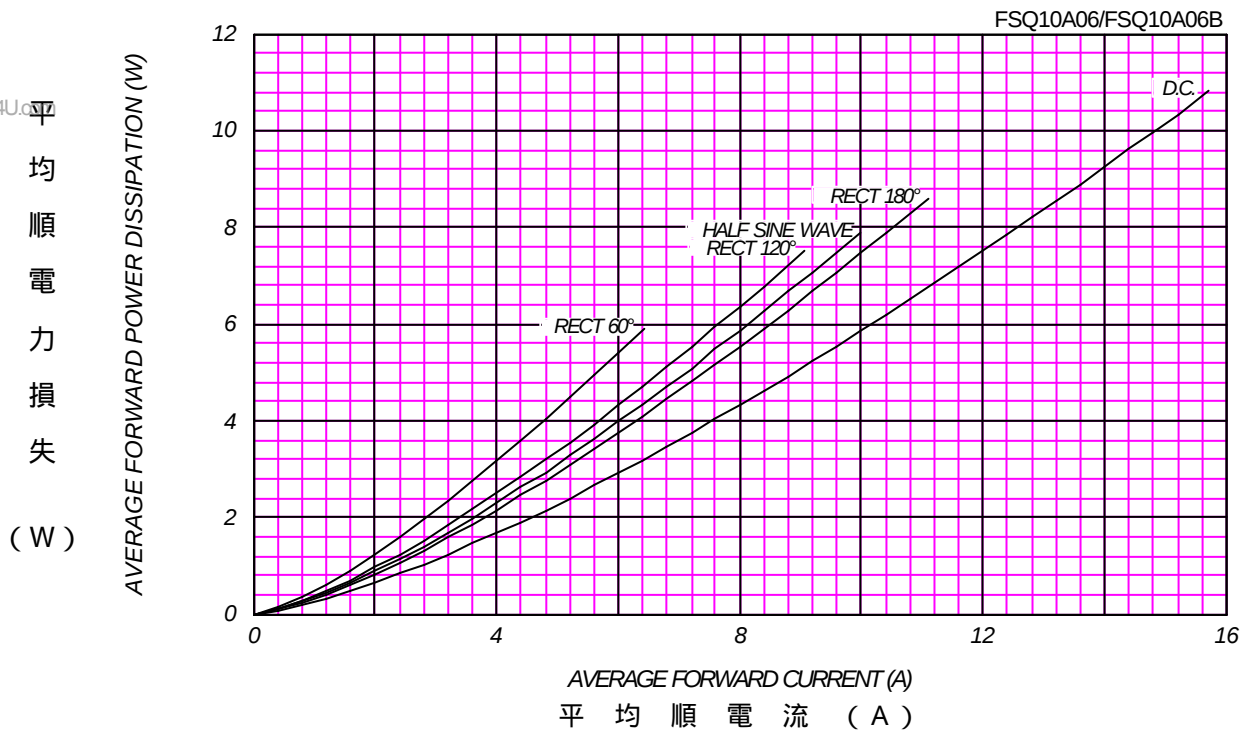
Single Chip



順電壓特性 FORWARD CURRENT VS. VOLTAGE

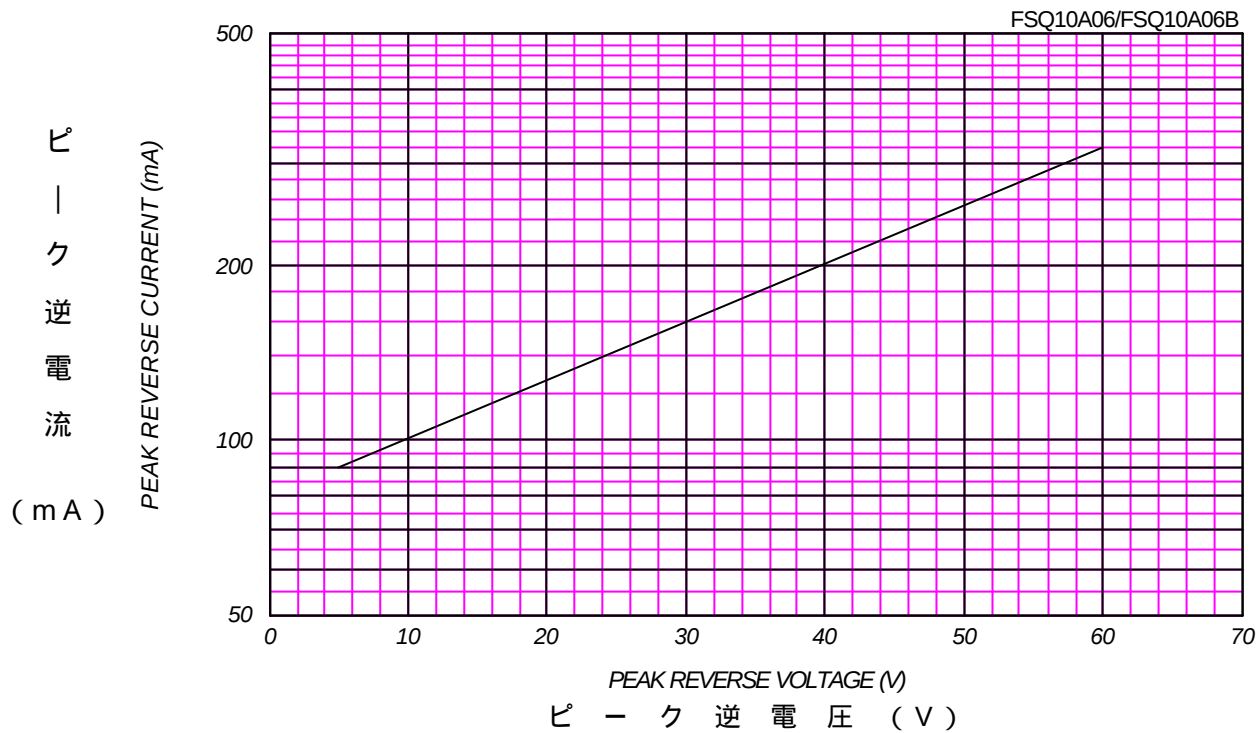


平均順電力損失特性 AVERAGE FORWARD POWER DISSIPATION

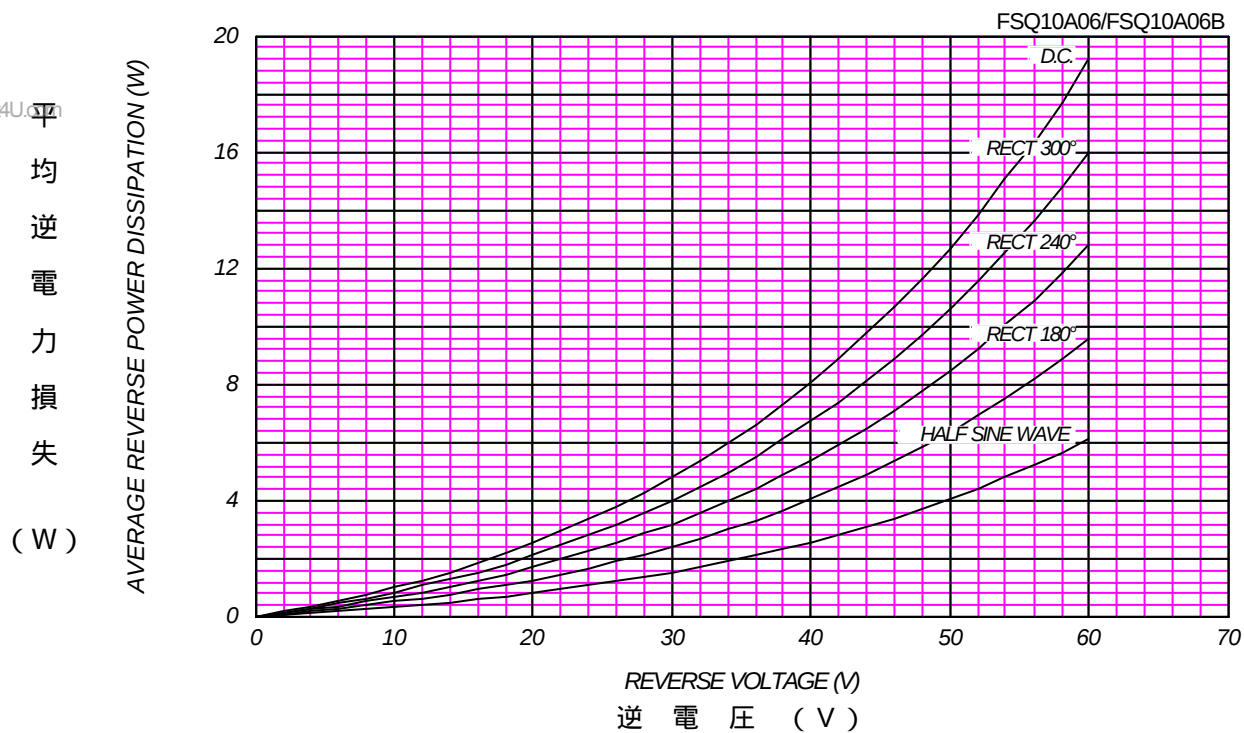


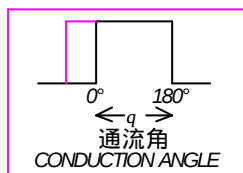
ピーク逆電流 - ピーク逆電圧特性
PEAK REVERSE CURRENT VS. PEAK REVERSE VOLTAGE

$T_j = 150^\circ\text{C}$



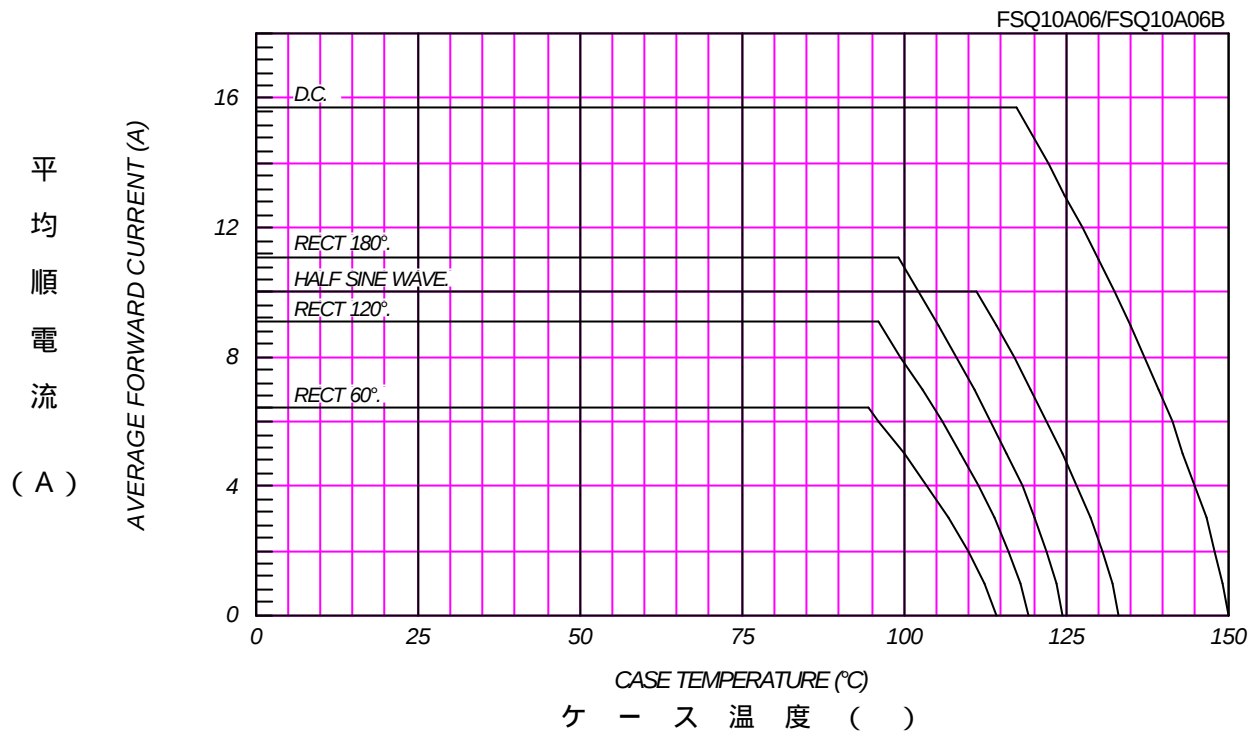
平均逆電力損失
AVERAGE REVERSE POWER DISSIPATION





平均順電流 - ケース温度定格

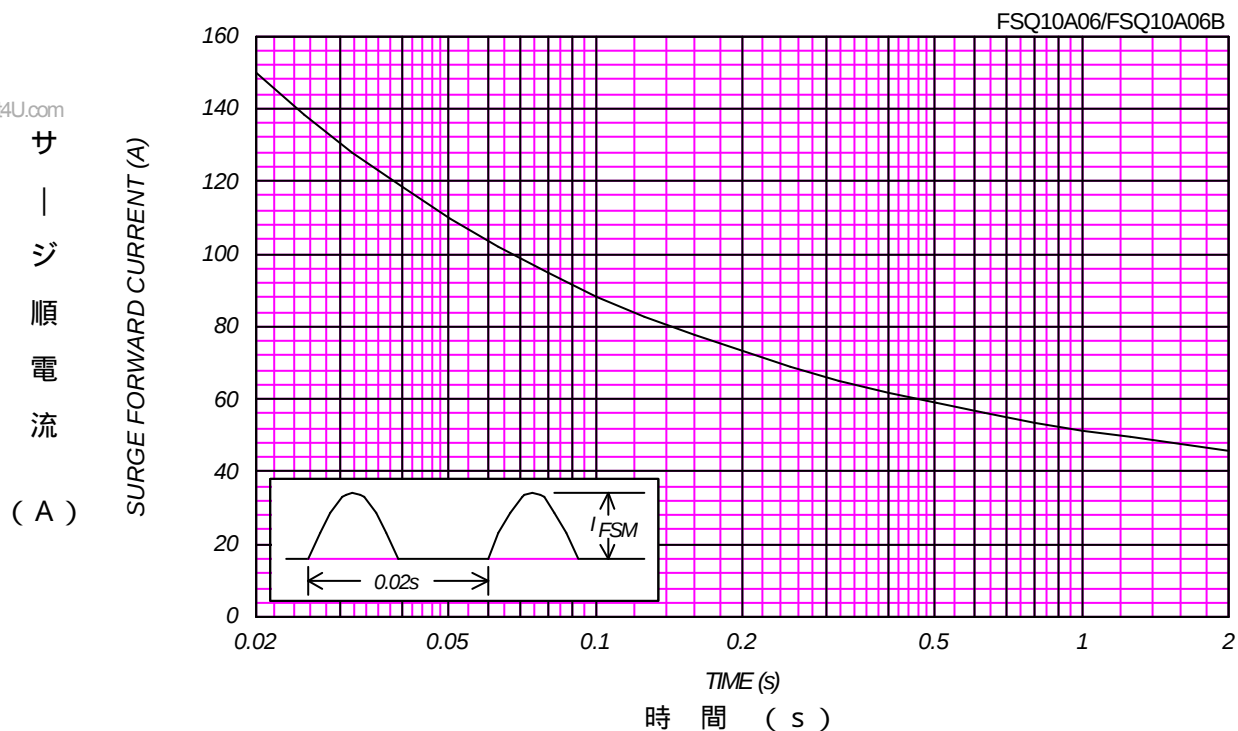
AVERAGE FORWARD CURRENT VS. CASE TEMPERATURE

V_{RM}=60V

サージ順電流定格

SURGE CURRENT RATINGS

f=50Hz, Half Sine Wave, Non-Repetitive, No Load



接 合 容 量 特 性
JUNCTION CAPACITANCE VS. REVERSE VOLTAGE

$T_j=25^{\circ}\text{C}$, $V_m=20\text{mV}_{\text{RMS}}$, $f=100\text{kHz}$, Typical Value

